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# Improved, SPST/SPDT Analog Switches 


#### Abstract

General Description Maxim's redesigned DG417/DG418/DG419 precision, CMOS, monolithic analog switches now feature guaranteed on-resistance matching ( $3 \Omega$ max) between switches and guaranteed on-resistance flatness over the signal range ( $4 \Omega \mathrm{max}$ ). These switches conduct equally well in either direction and guarantee low charge injection, low power consumption, and an ESD tolerance of 2000 V minimum per Method 3015.7. The new design offers low off-leakage current over temperature (less than 5 nA at $+85^{\circ} \mathrm{C}$ ). The DG417/DG418 are single-pole/single-throw (SPST) switches. The DG417 is normally closed, and the DG418 is normally open. The DG419 is single-pole/double-throw (SPDT) with one normally closed switch and one normally open switch. Switching times are less than 175ns max for ton and less than 145ns max for toff. Operation is from a single +10 V to +30 V supply, or bipolar $\pm 4.5 \mathrm{~V}$ to $\pm 20 \mathrm{~V}$ supplies. The improved DG417/DG418/DG419 are fabricated with a 44 V silicon-gate process.


## Applications

Sample-and-Hold Circuits
Test Equipment
Modems
Guidance and Control Systems
Audio Signal Routing
Communications Systems Battery-Operated Systems Fax Machines PBX, PABX
Military Radios

New Features

- Plug-In Upgrades for Industry-Standard DG417/DG418/DG419
- Improved RDS(ON) Match Between Channels ( $3 \Omega$ max, DG419 only)
- Guaranteed RFLAt(ON) Over Signal Range (4 $\Omega$ max)
- Improved Charge Injection (10pC max)
- Improved Off-Leakage Current Over Temperature ( $<5 \mathrm{nA}$ at $+85^{\circ} \mathrm{C}$ )
- Withstand Electrostatic Discharge (2000V min) per Method 3015.7
Existing Features
- Low RdS(ON) ( $35 \Omega$ max)
- Single-Supply Operation +10 V to +30 V

Bipolar-Supply Operation $\pm 4.5 \mathrm{~V}$ to $\pm 20 \mathrm{~V}$

- Low Power Consumption ( $35 \mu \mathrm{~W}$ max)
- Rail-to-Rail Signal Handling
- TTL/CMOS-Logic Compatible

Ordering Information

| PART | TEMP. RANGE | PIN-PACKAGE |
| :--- | ---: | :--- |
| DG417CJ | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | 8 Plastic DIP |
| DG417CY | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | 8 SO |
| DG417C/D | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | Dice |
| DG417DJ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 Plastic DIP |
| DG417DY | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 SO |

Ordering Information continued at end of data sheet.

* Contact factory for dice specifications.

Pin Configurations/Functional Diagrams/Truth Tables

N.C. $=$ NO INTERNAL CONNECTION


SWITCHES SHOWN FOR LOGIC "0" INPUT

## Improved, SPST/SPDT Analog Switches



| Continuous Power Dissipation ( $\mathrm{T}_{\mathrm{A}}=+70^{\circ} \mathrm{C}$ ) |  |
| :---: | :---: |
| DIP (derate $9.09 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $+70^{\circ} \mathrm{C}$ ) ............ 727 mW |  |
| SO (derate $5.88 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $+70^{\circ} \mathrm{C}$ ) | W |
| CERDIP (derate $8.00 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $+70^{\circ} \mathrm{C}$ ) ................ 640 mW |  |
| Operating Temperature Ranges |  |
| DG41_C_ .................................................. $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ |  |
| DG41_D_.................................................. $40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |
| DG41_AK |  |
| Storage Temperature Range .........................-65 ${ }^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |  |
| Lead Temperature (soldering, 10sec) | $+300^{\circ} \mathrm{C}$ |

Note 1: Signals on S, D, or IN exceeding V+ or V- are clamped by internal diodes. Limit forward current to maximum current ratings.
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ELECTRICAL CHARACTERISTICS—Dual Supplies

$\left(\mathrm{V}+=+15 \mathrm{~V}, \mathrm{~V}-=-15 \mathrm{~V}, \mathrm{VL}=5 \mathrm{~V}, \mathrm{GND}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{INL}}=0.8 \mathrm{~V}, \mathrm{~V}_{\mathrm{INH}}=2.4 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=\mathrm{T}_{\mathrm{MIN}}\right.$ to $\mathrm{T}_{\mathrm{MAX}}$, unless otherwise noted. $)$

| PARAMETER | SYMBOL | CONDITIONS |  |  |  | MIN | TYP <br> Note 2) | MAX | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SWITCH |  |  |  |  |  |  |  |  |  |
| Analog Signal Range | $\mathrm{V}_{\mathrm{S}}, \mathrm{V}_{\mathrm{D}}$ | (Note 3) |  |  |  | -15 |  | 15 | V |
| Drain-Source On-Resistance | RDS(ON) | $\begin{aligned} & \mathrm{V}_{+}=13.5 \mathrm{~V}, \mathrm{~V}-=-13.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{D}}= \pm 10 \mathrm{~V}, \\ & \mathrm{I}=-10 \mathrm{~mA} \end{aligned}$ |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | C, D |  | 20 | 35 | $\Omega$ |
|  |  |  |  | A |  | 20 | 30 |  |
|  |  |  |  | $\mathrm{T}_{\mathrm{A}}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ |  |  | 45 |  |
| On-Resistance Match Between Channels (Note 4) | $\Delta \mathrm{RDS}(\mathrm{ON})$ | $\begin{aligned} & \mathrm{V}_{+}=15 \mathrm{~V}, \mathrm{~V}-=-15 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{D}}= \pm 10 \mathrm{~V}, \\ & \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} \end{aligned}$ |  |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  |  |  | 3 | $\Omega$ |
|  |  |  |  | $\mathrm{T}_{\mathrm{A}}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ |  |  |  | 4 |  |  |
| On-Resistance Flatness (Note 4) | RFLAT(ON) | $\begin{aligned} & \mathrm{V}_{+}=15 \mathrm{~V}, \mathrm{~V}-=-15 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{D}}= \pm 5 \mathrm{~V}, \\ & \mathrm{I}_{\mathrm{S}}=-10 \mathrm{~mA} \end{aligned}$ |  | $\mathrm{TA}=+25^{\circ} \mathrm{C}$ |  |  |  | 4 | $\Omega$ |  |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ |  |  |  | 6 |  |  |
| Source-Off <br> Leakage Current (Note 5) | IS(OFF) | $\begin{aligned} & \mathrm{V}_{+}=16.5 \mathrm{~V}, \mathrm{~V}-=-16.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{D}}= \pm 15.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{S}}=\mp 15.5 \mathrm{~V} \end{aligned}$ |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  | -0.25 |  | 0.25 | nA |  |
|  |  |  |  | $\begin{aligned} & T_{A}=T_{\text {MIN }} \text { to } \\ & T_{\text {MAX }} \end{aligned}$ | C, D | -5 |  | 5 |  |  |
|  |  |  |  | A | -20 |  | 20 |  |  |
| Drain-Off <br> Leakage Current (Note 5) | ID(OFF) | $\begin{aligned} & V_{+}=16.5 \mathrm{~V}, \\ & V_{-}=-16.5 \mathrm{~V}, \\ & V_{D}= \pm 15.5 \mathrm{~V}, \\ & V_{S}=\mp 15.5 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & \text { DG417/ } \\ & \text { DG418 } \end{aligned}$ |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  | -0.25 | 0.1 | 0.25 | nA |
|  |  |  |  | $\mathrm{T}_{\mathrm{A}}=\mathrm{T}_{\text {MIN }}$ to | C, D | -5 |  | 5 |  |  |
|  |  |  |  | TMAX | A | -20 |  | 20 |  |  |
|  |  |  | DG419 | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  | -0.75 | -0.1 | 0.75 |  |  |
|  |  |  |  | $\begin{aligned} & \mathrm{T}_{A}=\mathrm{T}_{\text {MIN }} \text { to } \\ & \text { TMAX } \end{aligned}$ | C, D | -10 |  | 10 |  |  |
|  |  |  |  |  | A | -40 |  | 40 |  |  |
| Drain-On <br> Leakage Current (Note 5) | $\mathrm{ID}(\mathrm{ON})$ | $\begin{aligned} & V_{+}=16.5 \mathrm{~V}, \\ & \mathrm{~V}-=-16.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{D}}= \pm 15.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{S}}= \pm 15.5 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & \text { DG417/ } \\ & \text { DG418 } \end{aligned}$ | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  | -0.4 |  | 0.4 | nA |  |
|  |  |  |  | $\mathrm{T}_{\mathrm{A}}=\mathrm{T}_{\text {MIN }}$ to | C, D | -10 |  | 10 |  |  |
|  |  |  |  | TMAX | A | -40 |  | 40 |  |  |
|  |  |  | DG419 | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  | -0.75 |  | 0.75 |  |  |
|  |  |  |  | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}=\mathrm{T}_{\text {MIN }} \text { to } \\ & \mathrm{T}_{\text {MAX }} \end{aligned}$ | C, D | -10 |  | 10 |  |  |
|  |  |  |  |  | A | -40 |  | 40 |  |  |

## Improved, SPST/SPDT Analog Switches

## ELECTRICAL CHARACTERISTICS—Dual Supplies (continued)

$\left(\mathrm{V}+=+15 \mathrm{~V}, \mathrm{~V}-=-15 \mathrm{~V}, \mathrm{VL}=5 \mathrm{~V}, \mathrm{GND}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{INL}}=0.8 \mathrm{~V}, \mathrm{~V}_{\text {INH }}=2.4 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=\mathrm{T}_{\mathrm{MIN}}\right.$ to $\mathrm{T}_{\mathrm{MAX}}$, unless otherwise noted. $)$

| PARAMETER | SYMBOL | CONDITIONS |  |  | MIN | $\begin{gathered} \text { TYP } \\ \text { (Note 2) } \end{gathered}$ | MAX | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| LOGIC INPUT |  |  |  |  |  |  |  |  |
| Logic Input Current with Input Voltage High | linh | $\mathrm{V}_{\mathrm{IN}}=2.4 \mathrm{~V}$ |  |  | -0.5 | 0.005 | 0.5 | $\mu \mathrm{A}$ |
| Logic Input Current with Input Voltage Low | IINL | V IN $=0.8 \mathrm{~V}$ |  |  | -0.5 | 0.005 | 0.5 | $\mu \mathrm{A}$ |
| DYNAMIC |  |  |  |  |  |  |  |  |
| Turn-On Time | ton | DG417/DG418, $V_{D}= \pm 10 \mathrm{~V}$, Figure 2 |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  | 100 | 175 | ns |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ |  |  | 250 |  |
| Turn-Off Time | tofF | DG417/DG418, $V_{D}= \pm 10 \mathrm{~V}$, Figure 2 |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  | 60 | 145 | ns |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ |  |  | 210 |  |
| Transition Time | tTRANS | DG419, <br> $\mathrm{V}_{\mathrm{S}}= \pm 10 \mathrm{~V}$, Figure 3 |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  |  | 175 | ns |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ |  |  | 250 |  |
| Break-Before-Make Interval | tD | DG419, $\mathrm{V}_{\mathrm{S} 1}=\mathrm{V}_{\mathrm{S} 2}= \pm 10 \mathrm{~V}$, Figure 4, $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  |  | 5 | 13 |  | ns |
| Charge Injection (Note 3) | Q | VGEN $=0 \mathrm{~V}$, Figure $5, \mathrm{~T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  |  |  | 3 | 10 | pC |
| Off-Isolation Rejection Ratio (Note 6) | OIRR | $R_{L}=500 \Omega, C_{L}=5 p F, f=1 \mathrm{MHz}$, Figure $6, T_{A}=+25^{\circ} \mathrm{C}$ |  |  | 68 |  |  | dB |
| Crosstalk (Note 7) |  | DG419, $R_{L}=50 \Omega, C_{L}=5 p F, f=1 \mathrm{MHz}$, Figure 7, $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  |  | 85 |  |  | dB |
| Drain Off-Capacitance | $\mathrm{C}_{\text {d ( OFF) }}$ | $\mathrm{V}_{\mathrm{D}}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$, Figure $8, \mathrm{~T}_{A}=+25^{\circ} \mathrm{C}$ |  |  |  | 8 |  | pF |
| Source Off-Capacitance | Cs (OFF) | $\mathrm{V}_{\mathrm{D}}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$, Figure $8, \mathrm{~T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ |  |  |  | 8 |  | pF |
| Drain-Source On-Capacitance | CD (ON) or Cs (ON) | $V_{S}=0 V, f=1 M H z,$ <br> Figure 9, $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | DG417/DG418 |  |  | 30 |  | pF |
|  |  |  | DG419 |  |  | 35 |  |  |
| SUPPLY |  |  |  |  |  |  |  |  |
| Positive Supply Current | $1+$ | $\begin{aligned} & \mathrm{V}_{+}=16.5 \mathrm{~V}, \mathrm{~V}-=-16.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V} \text { or } 5 \mathrm{~V} \end{aligned}$ |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | -1 | -0.0001 | 1 | $\mu \mathrm{A}$ |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ | -5 |  | 5 |  |
| Negative Supply Current | I- | $\begin{aligned} & V_{+}=16.5 \mathrm{~V}, \mathrm{~V}-=-16.5 \mathrm{~V}, \\ & \mathrm{~V}_{\text {IN }}=0 \mathrm{~V} \text { or } 5 \mathrm{~V} \end{aligned}$ |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | -1 | -0.0001 | 1 | $\mu \mathrm{A}$ |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ | -5 |  | 5 |  |
| Logic Supply Current | IL | $\begin{aligned} & V_{+}=16.5 \mathrm{~V}, \mathrm{~V}-=-16.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V} \text { or } 5 \mathrm{~V} \end{aligned}$ |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | -1 | -0.0001 | 1 | $\mu \mathrm{A}$ |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to TMAX | -5 |  | 5 |  |
| Ground Current | IGND | $\begin{aligned} & \mathrm{V}_{+}=16.5 \mathrm{~V}, \mathrm{~V}-=-16.5 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V} \text { or } 5 \mathrm{~V} \end{aligned}$ |  | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | -1 | -0.0001 | 1 | $\mu \mathrm{A}$ |
|  |  |  |  | $\mathrm{T}_{\text {A }}=\mathrm{T}_{\text {MIN }}$ to $\mathrm{T}_{\text {MAX }}$ | -5 |  | 5 |  |

## Improved, SPST/SPDT Analog Switches

## ELECTRICAL CHARACTERISTICS—Single Supply

$\left(\mathrm{V}+=+12 \mathrm{~V}, \mathrm{~V}-=0 \mathrm{~V}, \mathrm{VL}=5 \mathrm{~V}, \mathrm{GND}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{INH}}=2.4 \mathrm{~V}, \mathrm{~V}_{\mathrm{INL}}=0.8 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}\right.$, unless otherwise noted.)

| PARAMETER | SYMBOL | CONDITIONS | MIN | $\begin{aligned} & \text { TYP } \\ & \text { (Note 2) } \end{aligned}$ | MAX | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SWITCH |  |  |  |  |  |  |
| Analog Signal Range | Vanalog | (Note 3) | 0 |  | 12 | V |
| Drain-Source On-Resistance | RDS(ON) | $\mathrm{IS}=-10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{D}}=3.8 \mathrm{~V}, \mathrm{~V}_{+}=10.8 \mathrm{~V}$ |  | 40 | 100 | $\Omega$ |
| DYNAMIC |  |  |  |  |  |  |
| Turn-On Time | ton | DG417/DG418, $\mathrm{V}_{\mathrm{D}}=8 \mathrm{~V}$, Figure 2 |  | 110 |  | ns |
| Turn-Off Time | toff | DG417/DG418, $\mathrm{V}_{\mathrm{D}}=8 \mathrm{~V}$, Figure 2 |  | 40 |  | ns |
| Break-Before-Make Interval | tD | DG419, RL = $1000 \Omega$, $C_{L}=35 p F$, Figure 4 |  | 60 |  | ns |
| Charge Injection (Note 3) | Q | $\mathrm{CL}_{\mathrm{L}}=10 \mathrm{nF}, \mathrm{V}_{\mathrm{GEN}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=0 \mathrm{~V}$, Figure 5 |  | 2 | 10 | pC |
| SUPPLY |  |  |  |  |  |  |
| Positive Supply Current | $1+$ | All channels on or off, $\mathrm{V}_{+}=13.2 \mathrm{~V}$, $\mathrm{V}_{\mathrm{L}}=5.25 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or 5 V |  | -0.0001 |  | $\mu \mathrm{A}$ |
| Negative Supply Current | I- | All channels on or off, $\mathrm{V}_{+}=13.2 \mathrm{~V}$, $\mathrm{V}_{\mathrm{L}}=5.25 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V} \text { or } 5 \mathrm{~V}$ |  | -0.0001 |  | $\mu \mathrm{A}$ |
| Logic Supply Current | IL | All channels on or off, $\mathrm{V}_{\mathrm{L}}=5.25 \mathrm{~V}$, V IN $=0 \mathrm{~V}$ or 5 V |  | -0.0001 |  | $\mu \mathrm{A}$ |
| Ground Current | IGND | All channels on or off, $\mathrm{V}_{\mathrm{L}}=5.25 \mathrm{~V}$, V IN $=0 \mathrm{~V}$ or 5 V |  | -0.0001 |  | $\mu \mathrm{A}$ |

Note 2: Typical values are for design aid only, are not guaranteed, and are not subject to production testing. The algebraic convention where the most negative value is a minimum and the most positive value a maximum is used in this data sheet.
Note 3: Guaranteed by design.
Note 4: On-resistance match between channels and flatness is guaranteed only with bipolar-supply operation. Flatness is defined as the difference between the maximum and the minimum value of on-resistance as measured at the extremes of the specified analog range.
Note 5: Leakage parameters $I_{S(O F F)} I_{D(O F F)}$, and $I_{D(O N)}$ are $100 \%$ tested at the maximum rated hot temperature and guaranteed by correlation at $+25^{\circ} \mathrm{C}$.
Note 6: Off-Isolation Rejection Ratio $=20 \mathrm{log}\left(\mathrm{V}_{\mathrm{D}} / \mathrm{V}_{\mathrm{S}}\right), \mathrm{V}_{\mathrm{D}}=$ output, $\mathrm{V}_{\mathrm{S}}=$ input to off switch.
Note 7: Between any two switches.

## Improved, SPST/SPDT Analog Switches

Typical Operating Characteristics
( $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$, unless otherwise noted.)


ON-RESISTANCE vs. $V_{D}$ AND TEM PERATURE



OFF-LEAKAGE CURRENT vs.
TEMPERATURE


ON-RESISTANCE vs. $V_{D}$ (SINGLE SUPPLY)


ON-LEAKAGE CURRENT vs. TEM PERATURE


CHARGE INJECTION vs.
ANALOG VOLTAGE


SUPPLY CURRENT vs.

TEMPERATURE


## Improved, SPST/SPDT Analog Switches

| PIN |  |  | NAME |  |
| :---: | :---: | :---: | :---: | :--- |
| DG417 | DG418 | DG419 |  |  |
| 1 | - | - | S | Analog-Switch Source Terminal (normally closed) |
| - | 1 | - | S | Analog-Switch Source Terminal (normally open) |
| - | - | 2 | S1 | Analog-Switch Source Terminal 1 (normally closed) |
| 2 | 2 | - | N.C. | No Internal Connection |
| 3 | 3 | 3 | GND | Logic Ground |
| 4 | 4 | 4 | V+ | Analog-Signal Positive Supply Input |
| 5 | 5 | 5 | VL | Logic-Level Positive Supply Input |
| 6 | 6 | 6 | IN | Logic-Level Input |
| 7 | 7 | 7 | V- | Analog-Signal Negative Supply Input |
| 8 | 8 | 1 | D | Analog-Switch Drain Terminal |
| - | - | 8 | S2 | Analog-Switch Source Terminal 2 (normally open) |

## Applications Information

Operation with Supply Voltages Other than $\pm 15 \mathrm{~V}$ Using supply voltages other than $\pm 15 \mathrm{~V}$ reduces the analog signal range. The DG417/DG418/DG419 switches operate with $\pm 4.5 \mathrm{~V}$ to $\pm 20 \mathrm{~V}$ bipolar supplies or with $\mathrm{a}+10 \mathrm{~V}$ to +30 V single supply; connect V - to 0 V when operating with a single supply. Also, all device types can operate with unbalanced supplies, such as +24 V and -5 V . VL must be connected to +5 V to be $T \mathrm{LL}$ compatible, or to $\mathrm{V}+$ for CMOS-logic level inputs. The Typical Operating Characteristics graphs show typical on-resistance with $\pm 20 \mathrm{~V}, \pm 15 \mathrm{~V}, \pm 10 \mathrm{~V}$, and $\pm 5 \mathrm{~V}$ supplies. (Switching times increase by a factor of two or more for operation at $\pm 5 \mathrm{~V}$.)

## Overvoltage Protection

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings may cause permanent damage to the devices. Always sequence $\mathrm{V}+$ on first, followed by VL , V -, and logic inputs. If power-supply sequencing is not possible, add two small, external signal diodes in series with the supply pins for overvoltage protection (Figure 1).


Figure 1. Overvoltage Protection Using External Blocking Diodes
Adding diodes reduces the analog signal range to 1 V below $\mathrm{V}+$ and 1 V above V -, without affecting low switch resistance and low leakage characteristics. Device operation is unchanged, and the difference between $\mathrm{V}+$ and V - should not exceed +44 V .

## Improved, SPST/SPDT Analog Switches



Figure 2. DG417/DG418 Switching Time


Figure 3. DG419 Transition Time

## Improved, SPST/SPDT Analog Switches



Figure 4. DG419 Break-Before-Make Interval


Figure 5. Charge Injection
$\qquad$

## Improved，SPST／SPDT Analog Switches

Test Circuits／Timing Diagrams（continued）


Figure 6．Off－Isolation Rejection Ratio


Figure 8．Drain－Source Off－Capacitance


Figure 7．DG419 Crosstalk


Figure 9．Drain－Source On－Capacitance

## Improved, SPST/SPDT Analog Switches

_Ordering Information (continued)

| PART | TEMP. RANGE | PIN-PACKAGE |
| :--- | :--- | :--- |
| DG417DK | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 CERDIP |
| DG417AK | $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 CERDIP** |
| DG418CJ | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | 8 Plastic DIP |
| DG418CY | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | 8 SO |
| DG418C/D | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | Dice |
| DG418DJ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 Plastic DIP |
| DG418DY | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 SO |
| DG418DK | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 CERDIP |
| DG418AK | $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 CERDIP* |
| DG419CJ | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | 8 Plastic DIP |
| DG419CY | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | 8 SO |
| DG419C/D | $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | Dice* |
| DG419DJ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 Plastic DIP |
| DG419DY | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 SO |
| DG419DK | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 8 CERDIP |
| DG419AK | $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 8 CERDIP** |

* Contact factory for dice specifications.
**Contact factory for availability and processing to MIL-STD-883B.


TRANSISTOR COUNT: 32
SUBSTRATE CONNECTED TO V+

| DIE PAD | DG417 | DG418 | DG419 |
| :---: | :---: | :---: | :---: |
| 1 | D | $\mathrm{N} . C$. | S |
| 2 | GND | GND | GND |
| 3 | $\mathrm{~V}+$ | $\mathrm{V}_{+}$ | $\mathrm{V}_{+}$ |
| 4 | VL | VL | VL |
| 5 | IN | IN | IN |
| 6 | $\mathrm{~V}-$ | $\mathrm{V}-$ | $\mathrm{V}-$ |
| 7 | $\mathrm{~N} . C$. | S | S |
| 8 | N.C. | D | D |
| 9 | S | N.C. | D |

## Improved, SPST/SPDT Analog Switches




## Improved, SPST/SPDT Analog Switches



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